

### FEATURES

- Low  $V_{CE(sat)}$  Device
- 10 $\mu$ s Short Circuit Withstand
- High Thermal Cycling Capability
- High Current Density Enhanced DMOS SPT
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- Isolated AISiC Base with AlN Substrates

### APPLICATIONS

- Choppers
- Motor Controllers
- Power Supplies
- Traction Auxiliaries

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM250PKM33-TL000 is a Low  $V_{CE(sat)}$  3300V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module configured with the upper arm of the bridge controlled. The IGBT has a wide reverse bias safe operating area (RBSOA). This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

### ORDERING INFORMATION

Order As:

### DIM250PKM33-TL000

Note: When ordering, please use the complete part number

### KEY PARAMETERS

$V_{CES}$	<b>3300V</b>
$V_{CE(sat)}$ * (typ)	<b>2.0V</b>
$I_C$ (max)	<b>250A</b>
$I_{C(PK)}$ (max)	<b>500A</b>

\* Measured at the auxiliary terminals

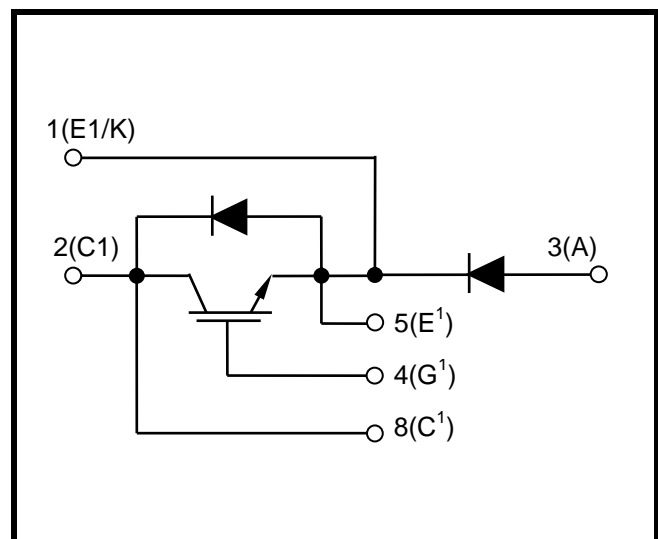
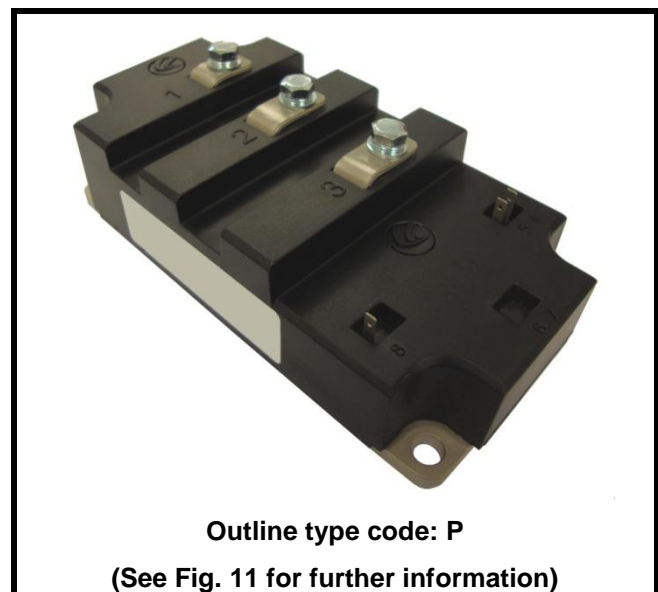


Fig. 1 Circuit configuration



Outline type code: P

(See Fig. 11 for further information)

Fig. 2 Package

## ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
$V_{CES}$	Collector-emitter voltage	$V_{GE} = 0\text{V}$	3300	V
$V_{GES}$	Gate-emitter voltage		$\pm 20$	V
$I_C$	Continuous collector current	$T_{case} = 115^{\circ}\text{C}$	250	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 140^{\circ}\text{C}$	500	A
$P_{max}$	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$ , $T_j = 150^{\circ}\text{C}$	2.6	kW
$I^2t$	Diode $I^2t$ value – IGBT Arm	$V_R = 0$ , $t_p = 10\text{ms}$ , $T_j = 150^{\circ}\text{C}$	20	$\text{kA}^2\text{s}$
	Diode $I^2t$ value – Diode Arm		20	$\text{kA}^2\text{s}$
$V_{isol}$	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
$Q_{PD}$	Partial discharge – per module	IEC1287, $V_1 = 3500\text{V}$ , $V_2 = 2600\text{V}$ , 50Hz RMS	10	pC

## THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	48	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode (IGBT Arm)	Continuous dissipation - junction to case	-	-	96	$^{\circ}\text{C}/\text{kW}$
	Thermal resistance – diode (Diode Arm)		-	-	96	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	16	$^{\circ}\text{C}/\text{kW}$
$T_j$	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	150	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M5	-	-	4	Nm

**ELECTRICAL CHARACTERISTICS**
 $T_{case} = 25^{\circ}\text{C}$  unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_{case} = 125^{\circ}\text{C}$			15	mA
		$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_{case} = 150^{\circ}\text{C}$			25	mA
$I_{GES}$	Gate leakage current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$			1	$\mu\text{A}$
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 20\text{mA}, V_{GE} = V_{CE}$		5.7		V
$V_{CE(sat)}^{\dagger}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{V}, I_C = 250\text{A}$		2.0		V
		$V_{GE} = 15\text{V}, I_C = 250\text{A}, T_j = 125^{\circ}\text{C}$		2.6		V
		$V_{GE} = 15\text{V}, I_C = 250\text{A}, T_j = 150^{\circ}\text{C}$		2.8		V
$I_F$	Diode forward current	DC		250		A
$I_{FM}$	Diode maximum forward current	$t_p = 1\text{ms}$		500		A
$V_F$	Diode forward voltage $^{\dagger}$ (IGBT arm)	$I_F = 250\text{A}$		2.4		V
	Diode forward voltage $^{\ddagger}$ (Diode arm)			2.5		V
	Diode forward voltage $^{\dagger}$ (IGBT arm)	$I_F = 250\text{A}, T_j = 125^{\circ}\text{C}$		2.5		V
	Diode forward voltage $^{\ddagger}$ (Diode arm)			2.6		V
	Diode forward voltage $^{\dagger}$ (IGBT arm)	$I_F = 250\text{A}, T_j = 150^{\circ}\text{C}$		2.4		V
	Diode forward voltage $^{\ddagger}$ (Diode arm)			2.5		V
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		45		nF
$Q_g$	Gate charge	$\pm 15\text{V}$ Including external $C_{ge}$		5		$\mu\text{C}$
$C_{res}$	Reverse transfer capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		1		nF
$L_M$	Module inductance			40		nH
$R_{INT}$	Internal transistor resistance			500		$\mu\Omega$
$SC_{Data}$	Short circuit current, $I_{SC}$	$T_j = 150^{\circ}\text{C}, V_{CC} = 2500\text{V}$ $t_p \leq 10\mu\text{s}, V_{GE} \leq 15\text{V}$ $V_{CE(max)} = V_{CES} - L^* \times dl/dt$ IEC 60747-9		950		A

**Note:**
 $^{\dagger}$  Measured at the auxiliary terminals

 $^{\ddagger}$  Measured at the power busbars

 $*$  L is the circuit inductance +  $L_M$

## ELECTRICAL CHARACTERISTICS

$T_{\text{case}} = 25^{\circ}\text{C}$  unless stated otherwise

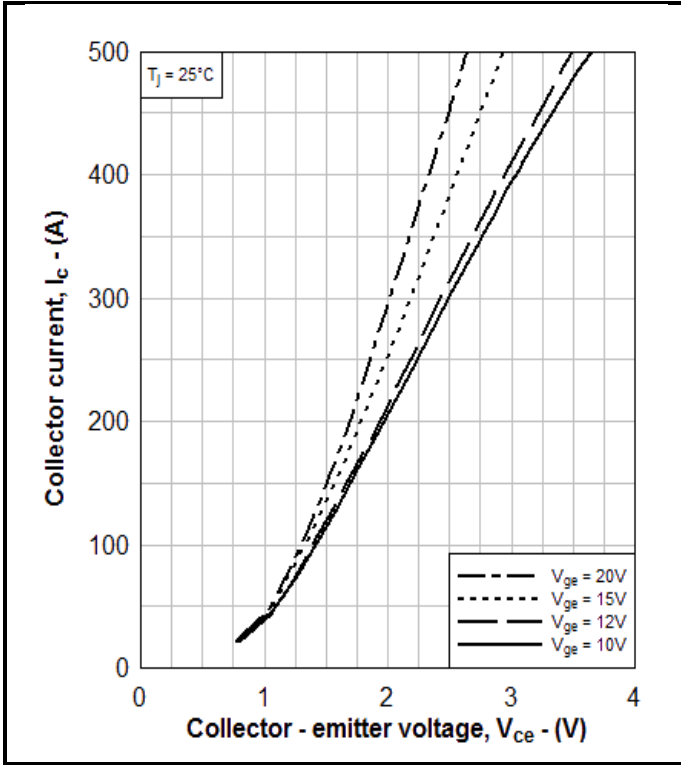
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 250\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{g(\text{ON})} = 10\Omega$ $R_{g(\text{OFF})} = 10\Omega$ $C_{GE} = 56\text{nF}$ $L_S \sim 150\text{nH}$		2700		ns
$t_f$	Fall time			610		ns
$E_{\text{OFF}}$	Turn-off energy loss			650		mJ
$t_{d(\text{on})}$	Turn-on delay time			960		ns
$t_r$	Rise time			430		ns
$E_{\text{ON}}$	Turn-on energy loss			400		mJ
$Q_{\text{rr}}$	Diode reverse recovery charge	$I_F = 250\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 700\text{A}/\mu\text{s}$		140		$\mu\text{C}$
$I_{\text{rr}}$	Diode reverse recovery current			150		A
$E_{\text{rec}}$	Diode reverse recovery energy			170		mJ

$T_{\text{case}} = 125^{\circ}\text{C}$  unless stated otherwise

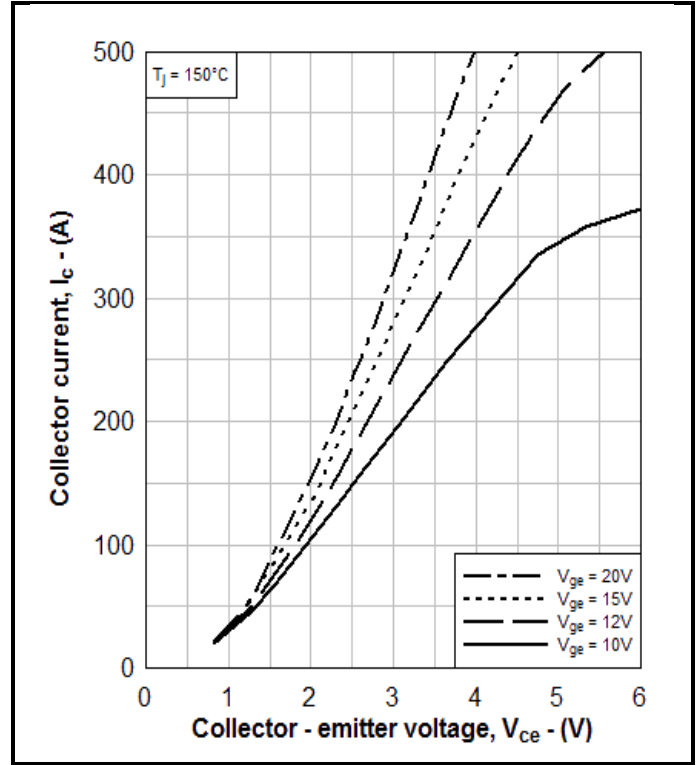
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 250\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{g(\text{ON})} = 10\Omega$ $R_{g(\text{OFF})} = 10\Omega$ $C_{GE} = 56\text{nF}$ $L_S \sim 150\text{nH}$		2750		ns
$t_f$	Fall time			590		ns
$E_{\text{OFF}}$	Turn-off energy loss			680		mJ
$t_{d(\text{on})}$	Turn-on delay time			1000		ns
$t_r$	Rise time			460		ns
$E_{\text{ON}}$	Turn-on energy loss			520		mJ
$Q_{\text{rr}}$	Diode reverse recovery charge	$I_F = 250\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 700\text{A}/\mu\text{s}$		230		$\mu\text{C}$
$I_{\text{rr}}$	Diode reverse recovery current			190		A
$E_{\text{rec}}$	Diode reverse recovery energy			280		mJ

$T_{\text{case}} = 150^{\circ}\text{C}$  unless stated otherwise

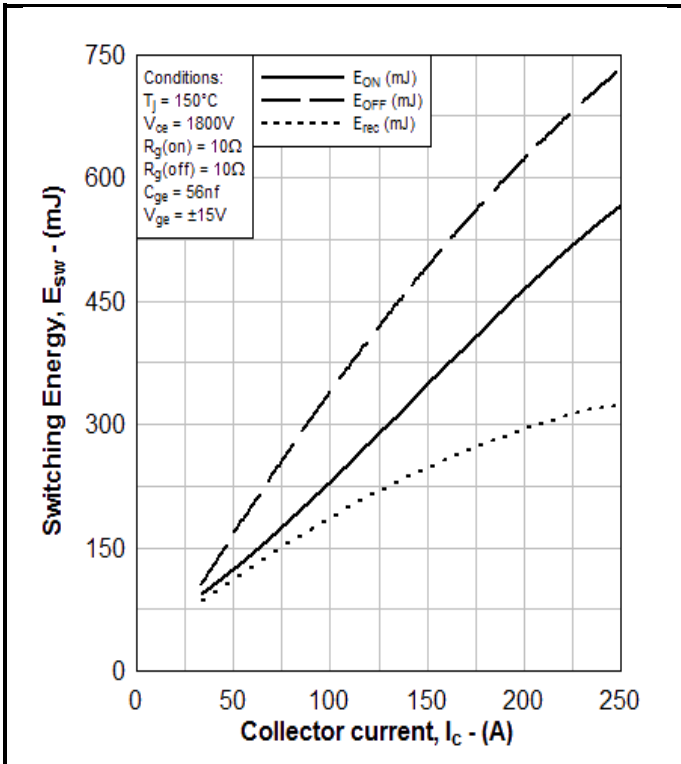
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 250\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 1800\text{V}$ $R_{g(\text{ON})} = 10\Omega$ $R_{g(\text{OFF})} = 10\Omega$ $C_{GE} = 56\text{nF}$ $L_S \sim 150\text{nH}$		2760		ns
$t_f$	Fall time			590		ns
$E_{\text{OFF}}$	Turn-off energy loss			750		mJ
$t_{d(\text{on})}$	Turn-on delay time			940		ns
$t_r$	Rise time			460		ns
$E_{\text{ON}}$	Turn-on energy loss			550		mJ
$Q_{\text{rr}}$	Diode reverse recovery charge	$I_F = 250\text{A}$ $V_{CE} = 1800\text{V}$ $di_F/dt = 700\text{A}/\mu\text{s}$		270		$\mu\text{C}$
$I_{\text{rr}}$	Diode reverse recovery current			200		A
$E_{\text{rec}}$	Diode reverse recovery energy			330		mJ



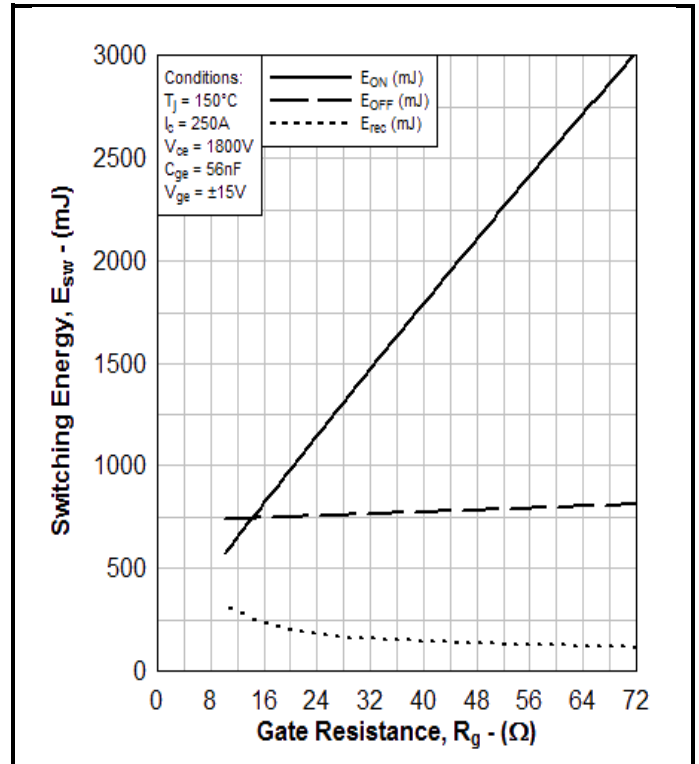
**Fig. 3 Typical output characteristics**



**Fig. 4 Typical output characteristics**



**Fig. 5 Typical switching energy vs collector current**



**Fig. 6 Typical switching energy vs gate resistance**

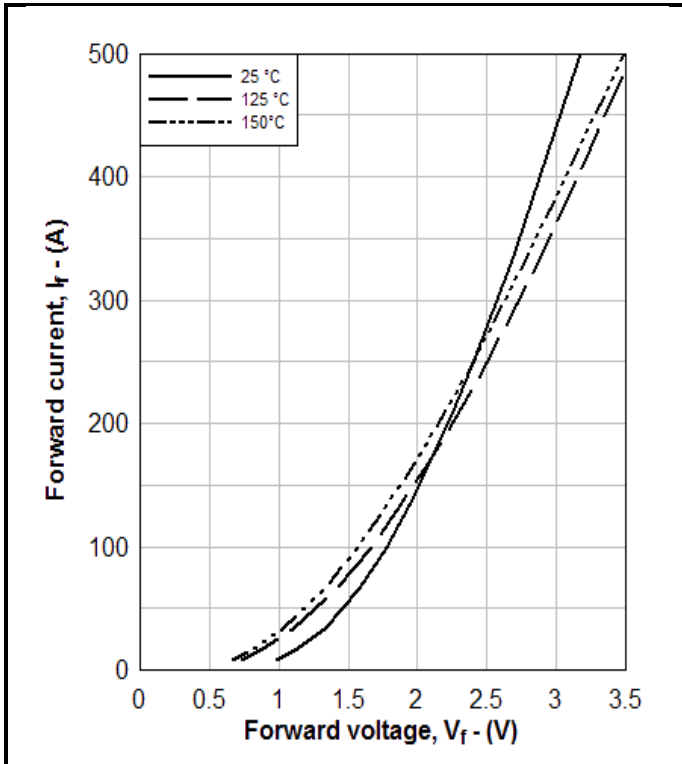


Fig. 7 Diode typical forward characteristics

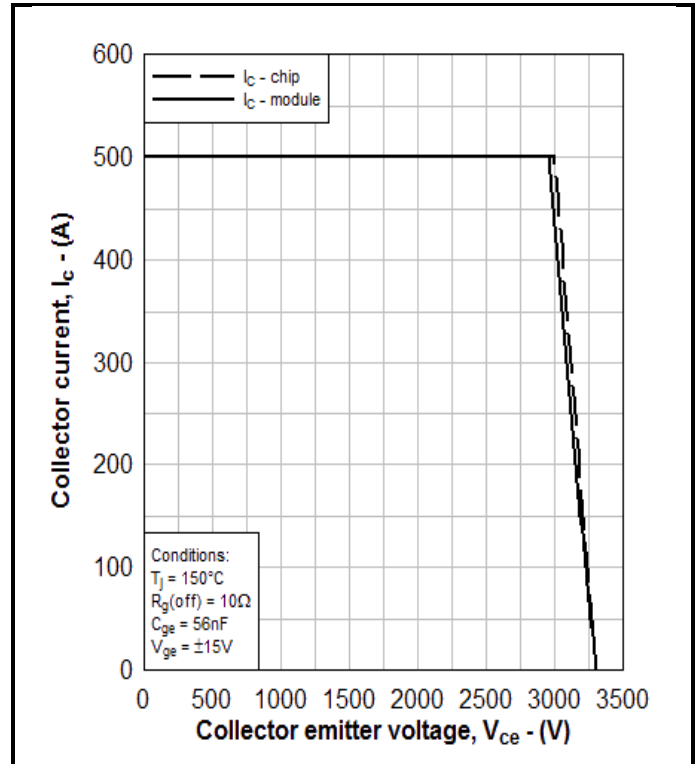


Fig. 8 Reverse bias safe operating area

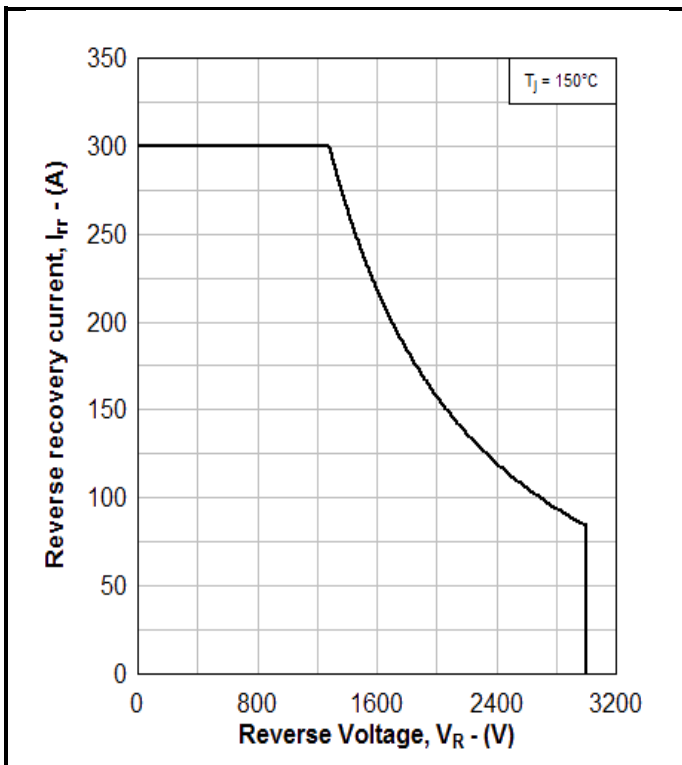


Fig. 9 Diode reverse bias safe operating area

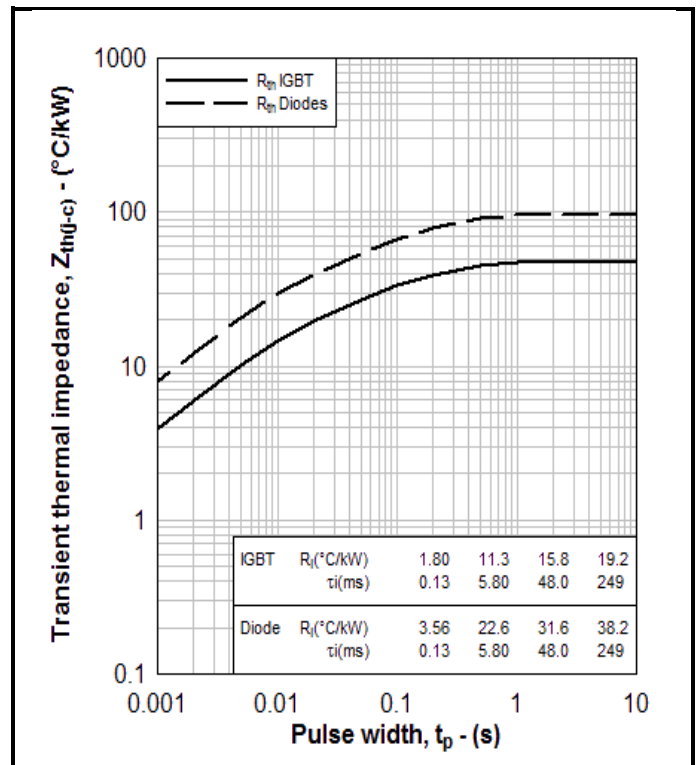
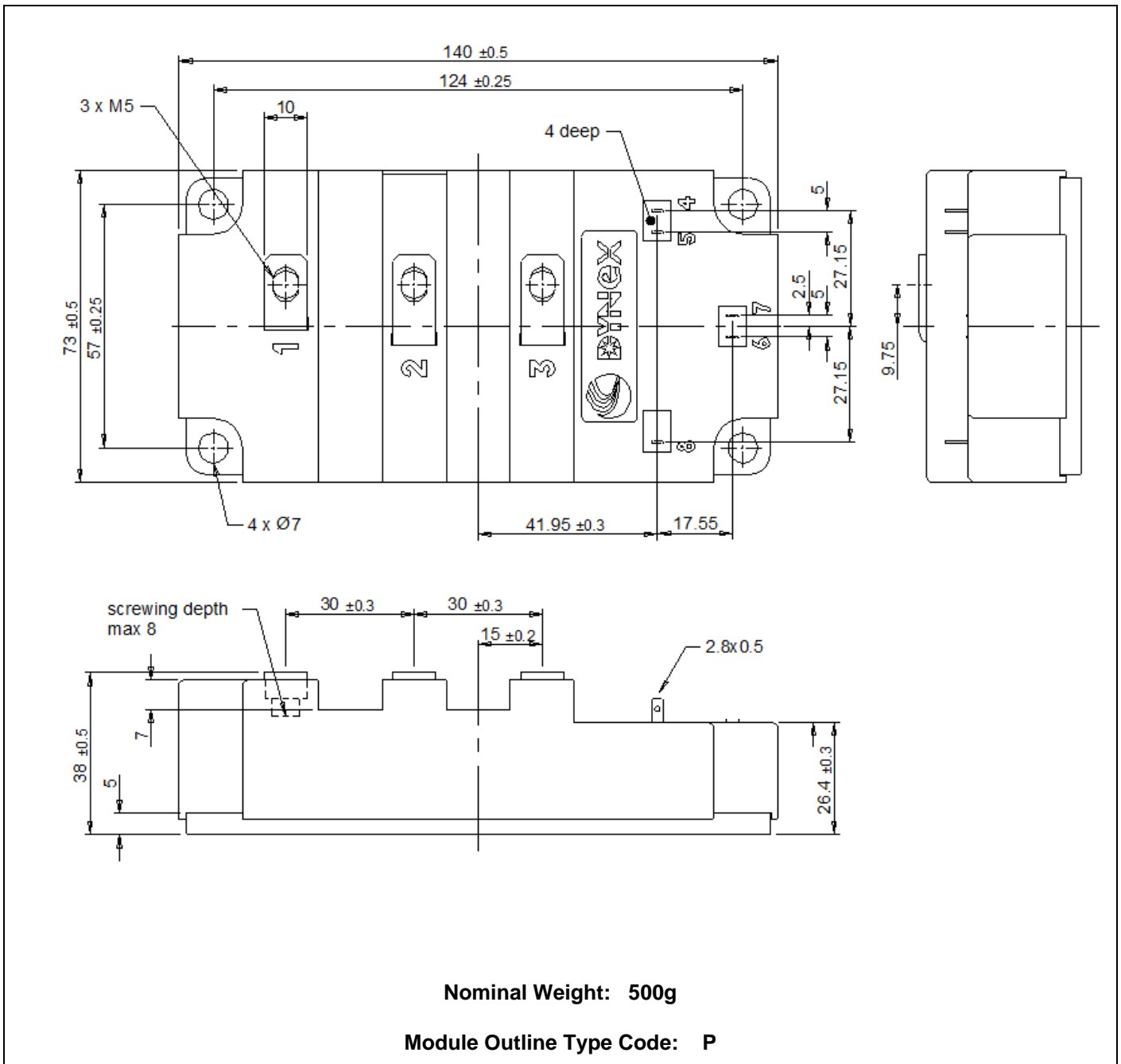


Fig. 10 Transient thermal impedance

**PACKAGE DETAILS**

For further package information, please visit our website or contact Customer Services.  
 All dimensions in mm, unless stated otherwise.  
**DO NOT SCALE.**


**Fig. 11 Module outline drawing**

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